

7NM60-U2

Power MOSFET

7.0A, 600V N-CHANNEL SUPER-JUNCTION MOSFET

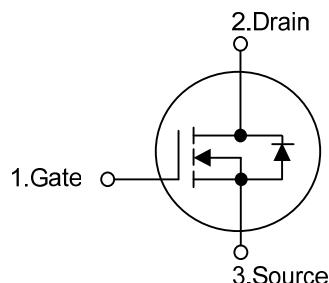
■ DESCRIPTION

The UTC **7NM60-U2** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in high speed switching applications at power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

■ FEATURES

- * $R_{DS(ON)} \leq 0.93 \Omega$ @ $V_{GS}=10V$, $I_D=3.5A$
- * Fast Switching Capability
- * Improved dv/dt Capability, High Ruggedness

■ SYMBOL

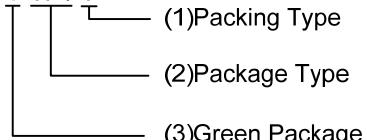


■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
7NM60L-TF1-T	7NM60G-TF1-T	TO-220F1	G	D	S	Tube
7NM60L-TM3-T	7NM60G-TM3-T	TO-251	G	D	S	Tube
7NM60L-TMS-T	7NM60G-TMS-T	TO-251S	G	D	S	Tube
7NM60L-TMS2-T	7NM60G-TMS2-T	TO-251S2	G	D	S	Tube
7NM60L-TN3-R	7NM60G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

7NM60G-TF1-T

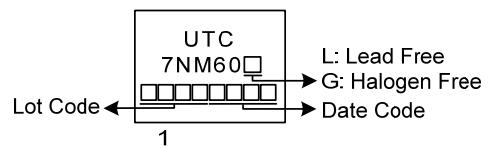


(1) T: Tube, R: Tape Reel

(2) TF1: TO-220F1, TM3: TO-251, TMS: TO-251S,
TMS2: TO-251S2, TN3: TO-252

(3) G: Halogen Free and Lead Free, L: Lead Free,

■ MARKING



7NM60-U2

Power MOSFET

■ ABSOLUTE MAXIMUM RATINGS ($T_c = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous $T_c=25^\circ\text{C}$	I_D	7	A
			4.5	
	Pulsed (Note 2)	I_{DM}	21	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	144	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4	V/ns
Power Dissipation	TO-220F1	P_D	25	W
	TO-251/TO-251S		50	W
	TO-251S2/TO-252			
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L=100\text{mH}$, $I_{AS}=1.7\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\ \Omega$, Starting $T_J = 25^\circ\text{C}$.

4. $I_{SD} \leq 7.0\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$.

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220F1	θ_{JA}	62.5	$^\circ\text{C/W}$
	TO-251/TO-251S		110	$^\circ\text{C/W}$
	TO-251S2/TO-252			
Junction to Case	TO-220F1	θ_{JC}	5.0	$^\circ\text{C/W}$
	TO-251/TO-251S		2.5(Note)	$^\circ\text{C/W}$
	TO-251S2/TO-252			

Note: The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.



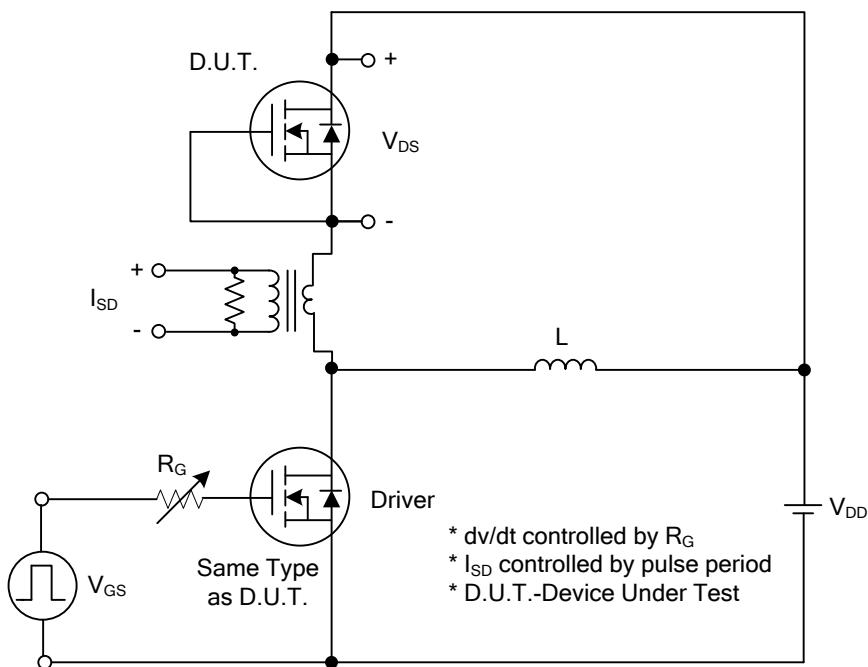
ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	600			V
Drain-Source Leakage Current	I_{DSS}	$V_{\text{DS}}=600\text{V}, V_{\text{GS}}=0\text{V}$		10		μA
Gate-Source Leakage Current	Forward	$V_{\text{GS}}=30\text{V}, V_{\text{DS}}=0\text{V}$		100		nA
	Reverse	$V_{\text{GS}}=-30\text{V}, V_{\text{DS}}=0\text{V}$		-100		
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{\text{GS}(\text{TH})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	2.5		4.5	V
Static Drain-Source On-State Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=3.5\text{A}$			0.93	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=50\text{V}, f=1.0\text{MHz}$		336		pF
Output Capacitance	C_{OSS}			68		pF
Reverse Transfer Capacitance	C_{RSS}			6		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge (Note 1)	Q_G	$V_{\text{DS}}=480\text{V}, V_{\text{GS}}=10\text{V}, I_{\text{D}}=7.0\text{A}$ (Note 1, 2)		23.5		nC
Gate to Source Charge	Q_{GS}			9		nC
Gate to Drain Charge	Q_{GD}			7.5		nC
Turn-ON Delay Time (Note 1)	$t_{\text{D}(\text{ON})}$	$V_{\text{DD}}=100\text{V}, V_{\text{GS}}=10\text{V},$ $I_{\text{D}}=7.0\text{A}, R_{\text{G}}=25\Omega$ (Note 1, 2)		6		ns
Rise Time	t_R			19		ns
Turn-OFF Delay Time	$t_{\text{D}(\text{OFF})}$			36		ns
Fall-Time	t_F			26		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S				7.0	A
Maximum Body-Diode Pulsed Current	I_{SM}				21	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	$I_S=7.0\text{A}, V_{\text{GS}}=0\text{V}$			1.4	V
Body Diode Reverse Recovery Time (Note 1)	t_{rr}	$I_S=7.0\text{A}, V_{\text{GS}}=0\text{V},$ $dI_F/dt=100\text{A}/\mu\text{s}$		265		ns
Body Diode Reverse Recovery Charge	Q_{rr}			2.9		μC

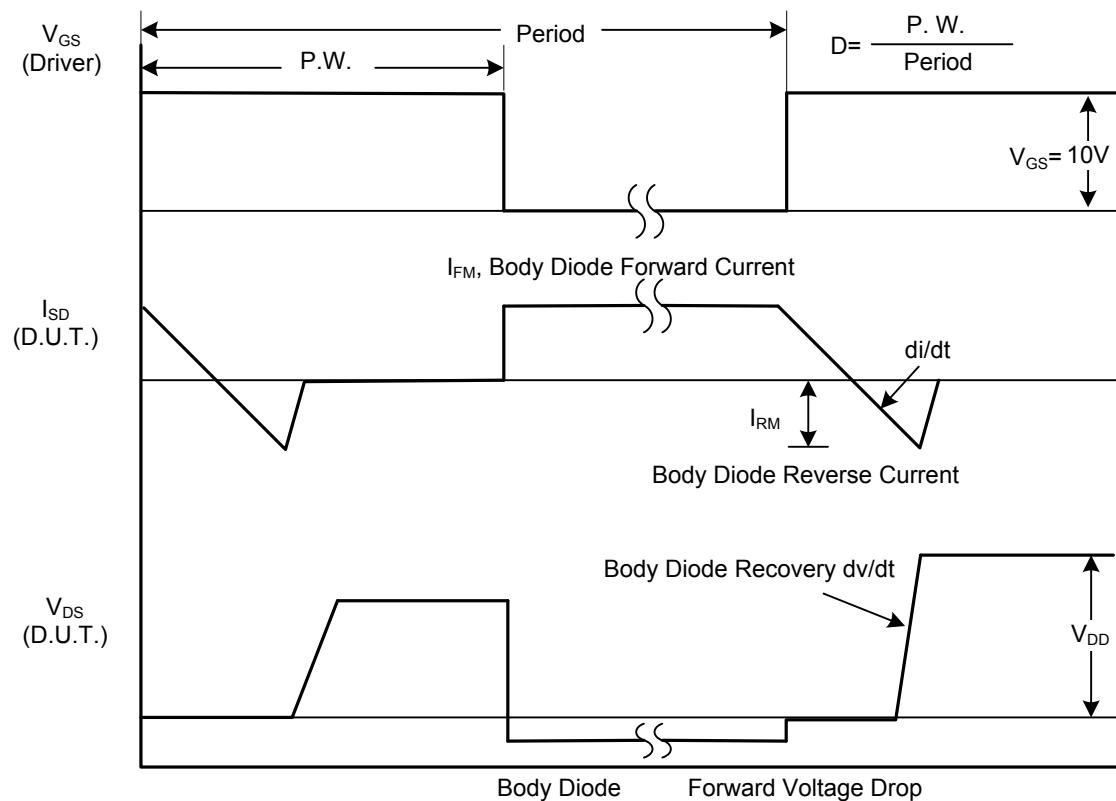
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

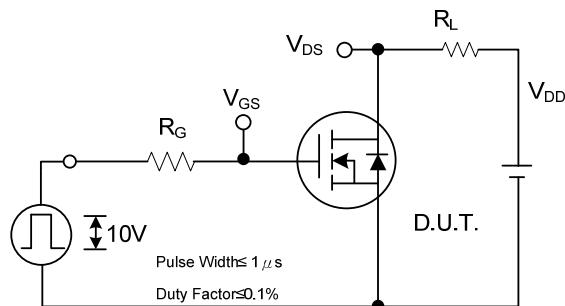


Peak Diode Recovery dv/dt Test Circuit

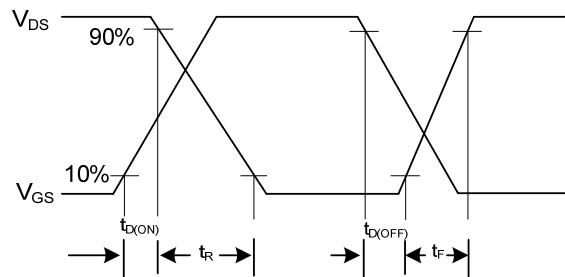


Peak Diode Recovery dv/dt Waveforms

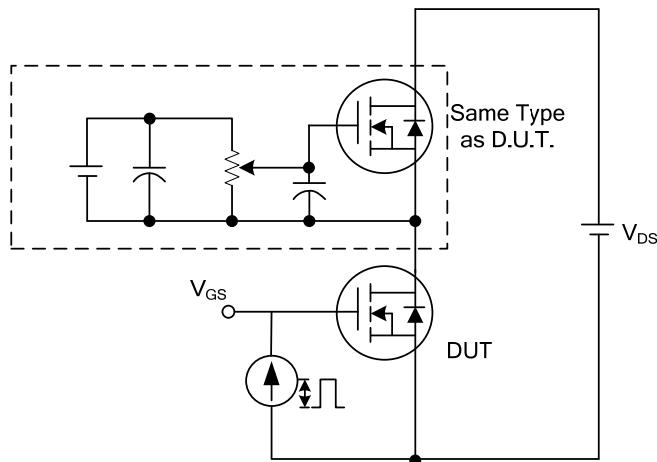
■ TEST CIRCUITS AND WAVEFORMS



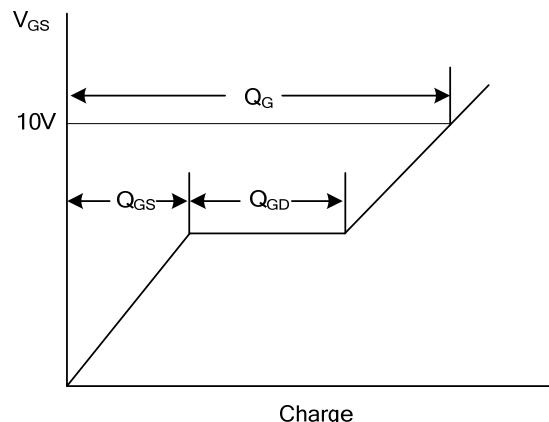
Switching Test Circuit



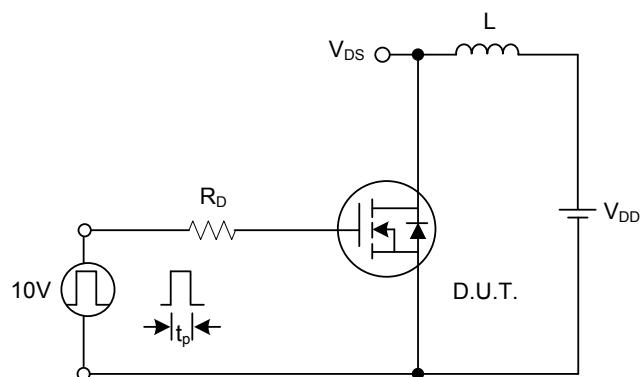
Switching Waveforms



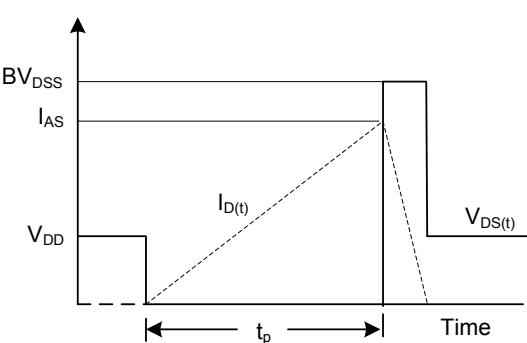
Gate Charge Test Circuit



Gate Charge Waveform

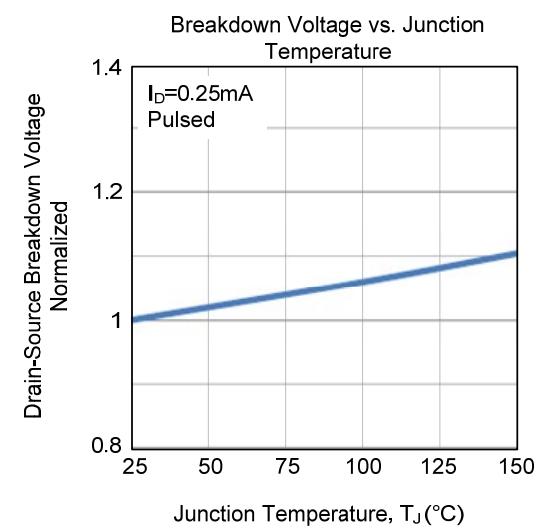
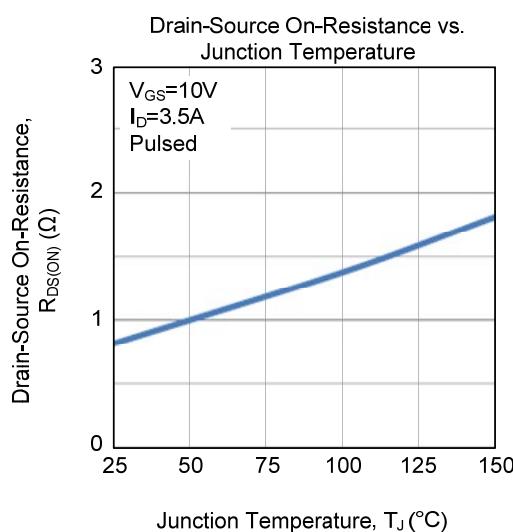
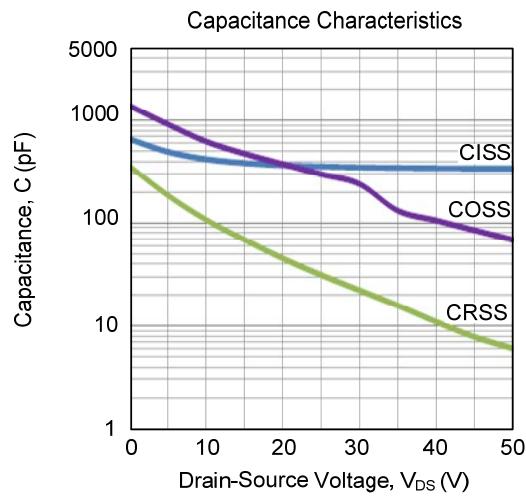
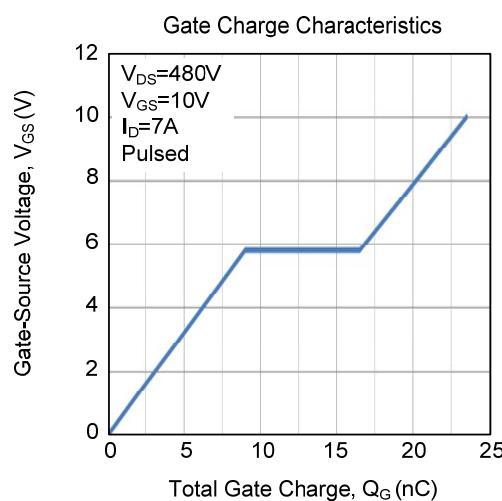
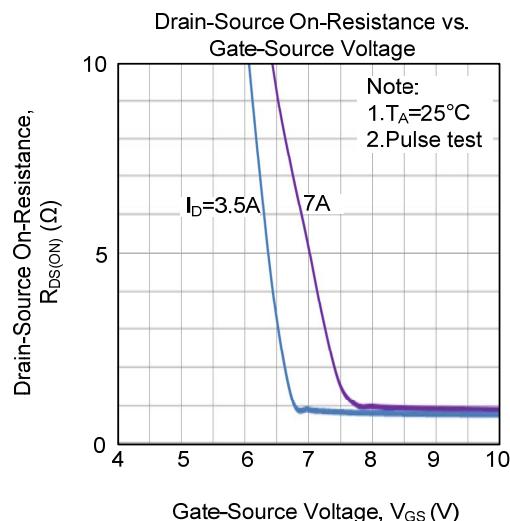
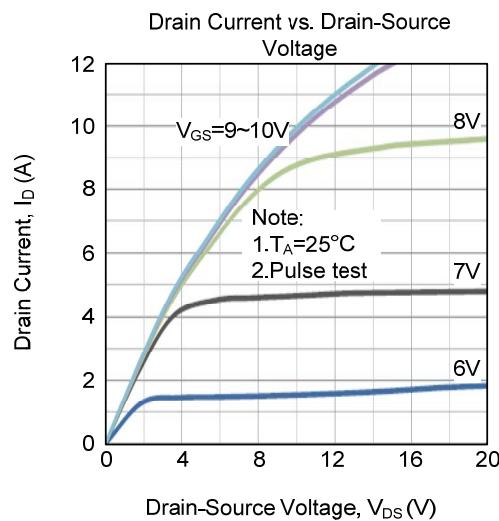


Unclamped Inductive Switching Test Circuit

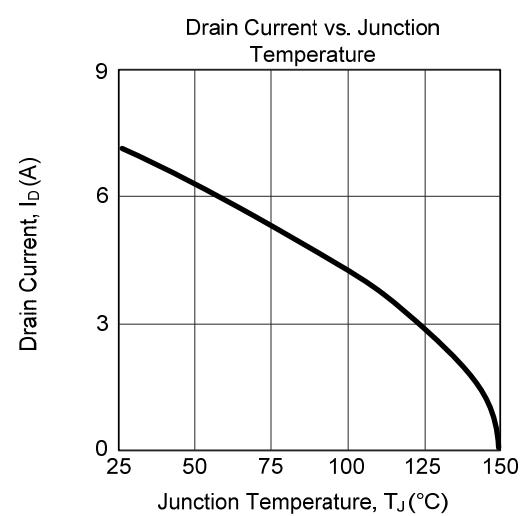
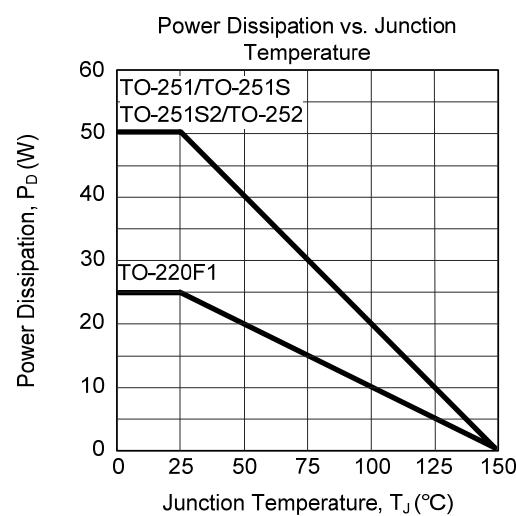
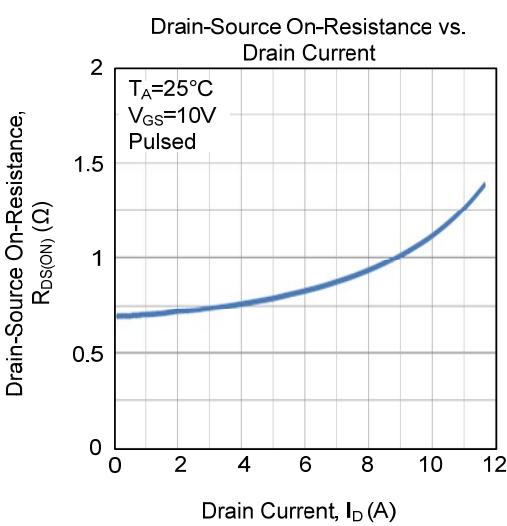
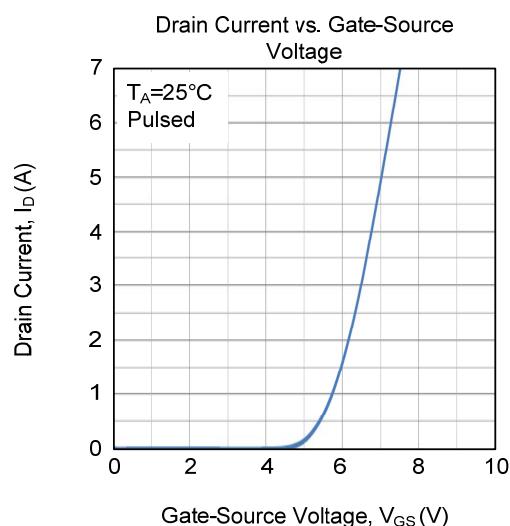
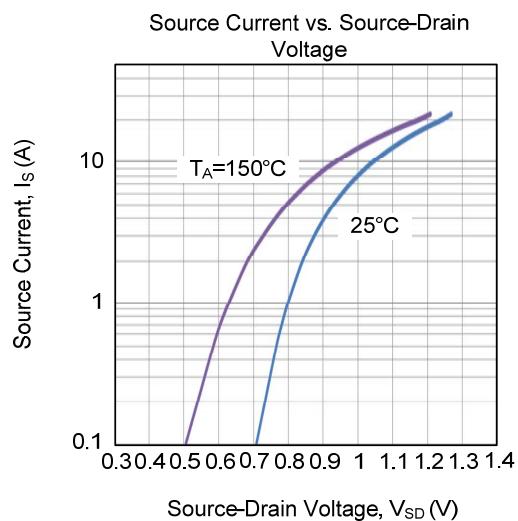
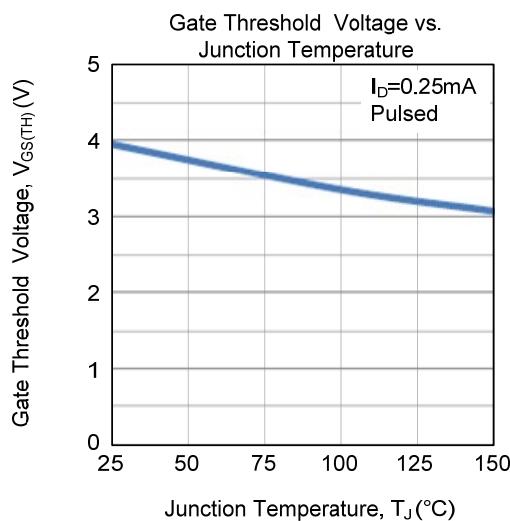


Unclamped Inductive Switching Waveforms

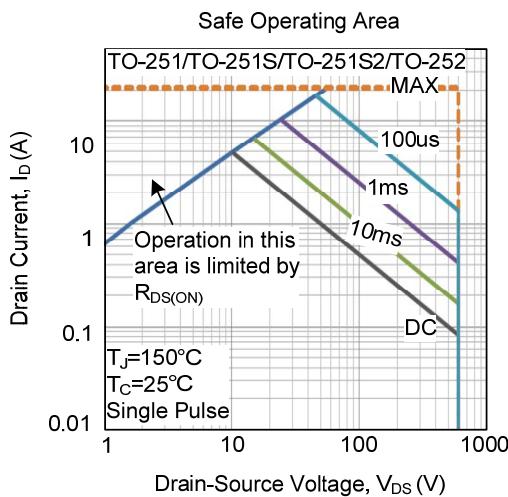
■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



- TYPICAL CHARACTERISTICS (Cont.)



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